

Electronic Supporting Information

Improvement in the thermoelectric performance of highly reproducible *n*-type (Bi,Sb)₂Se₃ alloys by Cl-doping

Nadra Nasir^{a,†}, Kyu Hyoung Lee^{b,†}, Sang-il Kim^c, Hyun-Sik Kim^d, Jae-Hong Lim^e, Liangwei Fu^{a,*}, Sung Wng Kim^{a,e,*}

1. The lattice parameters of Cl-doped BiSbSe₃.

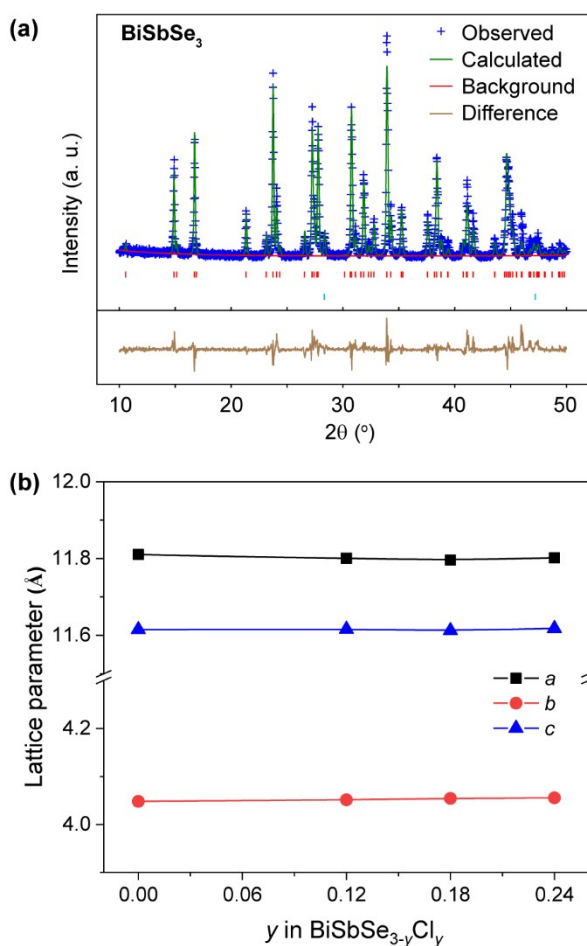


Figure S1. (a) One typical XRD refinement result of BiSbSe₃ sample. (b) The change in lattice parameters (*a*, *b*, and *c*) of orthorhombic BiSbSe₃ by Cl-doping.

2. Microstructure analysis for the SPSed $\text{BiSbSe}_{3-y}\text{Cl}_y$ ($y = 0, 0.12, 0.18, 0.24$) and $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{3-z}\text{Cl}_z$ ($z = 0, 0.12, 0.18, 0.24$) samples.

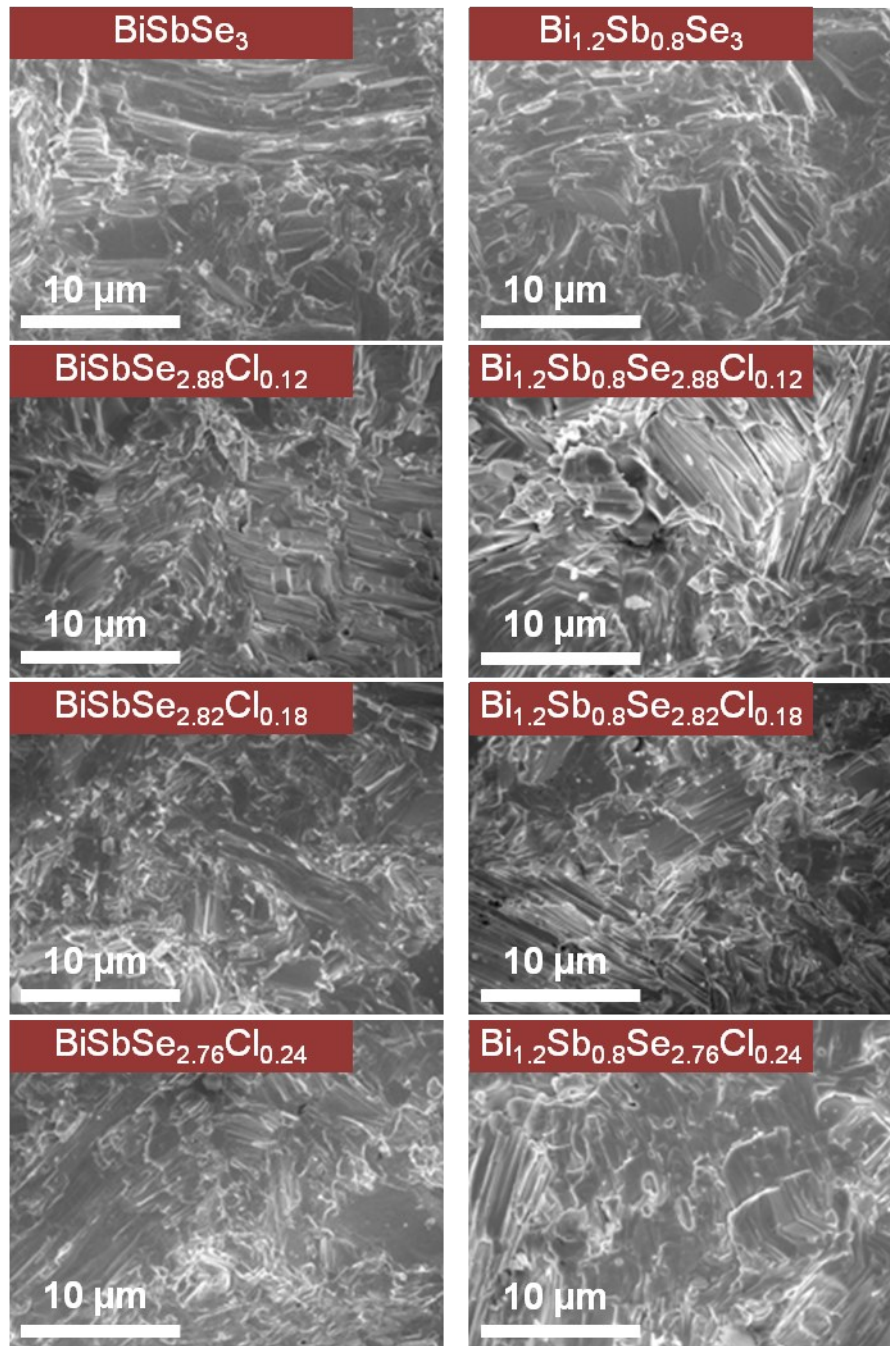


Figure S2. SEM images of fractured surfaces for the SPSed $\text{BiSbSe}_{3-y}\text{Cl}_y$ ($y = 0, 0.12, 0.18, 0.24$) and $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{3-z}\text{Cl}_z$ ($z = 0, 0.12, 0.18, 0.24$).

3. The mole fraction of rhombohedral phase in $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{3-z}\text{Cl}_z$ ($z = 0, 0.12, 0.18, 0.24$).

Table S1. The mole fraction of rhombohedral phase in $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{3-z}\text{Cl}_z$ ($z = 0, 0.12, 0.18, 0.24$), which is calculated by Rietveld refinement. The relative densities of the samples measured by the Archimedes principle (AlfaMiracle, MD-300S) are also shown.

Compositions (nominal)	Mole fraction		Relative density (%)
	Rhombohedral	Orthorhombic	
$\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_3$	0.743	0.257	97.4%
$\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{2.88}\text{Cl}_{0.12}$	0.744	0.256	97.4%
$\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{2.82}\text{Cl}_{0.18}$	0.745	0.255	95.5%
$\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{2.76}\text{Cl}_{0.24}$	0.747	0.253	97.1%

4. The lattice parameters of Cl-doped $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_3$.

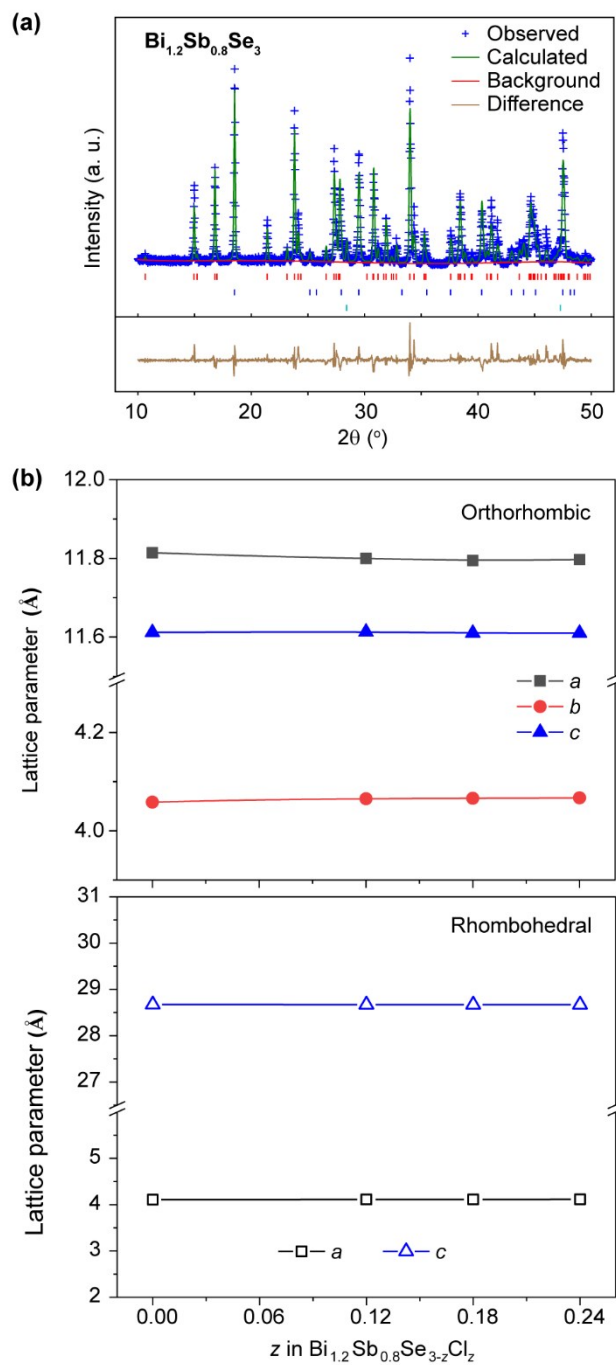


Figure S3. (a) One typical XRD refinement result of $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_3$ sample. (b) The change in lattice parameters of rhombohedral (a and c) and orthorhombic (a , b , and c) phases of $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_3$ by Cl-doping.

5. Phase formation in $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{2.7}\text{Cl}_{0.3}$.

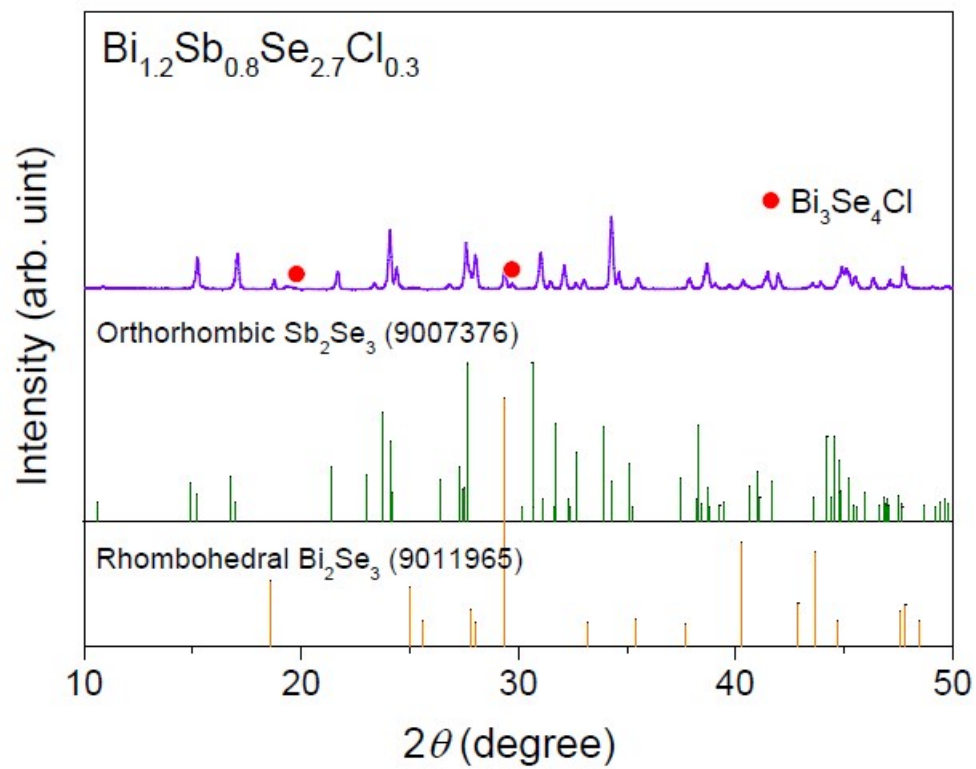


Figure S4. XRD pattern of SPSed $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_{2.7}\text{Cl}_{0.3}$.

6. Calculation of electronic thermal conductivity

The electronic thermal conductivity (κ_{ele}) is estimated by the Wiedemann-Franz law ($\kappa_{ele} = L\sigma T$, where L , σ , and T are the Lorenz number, electrical conductivity, and the absolute temperature). Temperature dependent L is obtained by using Eq. S1 assuming a single parabolic band model [1].

$$L = 1.5 + \exp\left(-\frac{|S|}{116}\right) \quad (S1)$$

Figure S5 shows the temperature dependences of L for Cl-doped BiSbSe_3 and $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_3$.

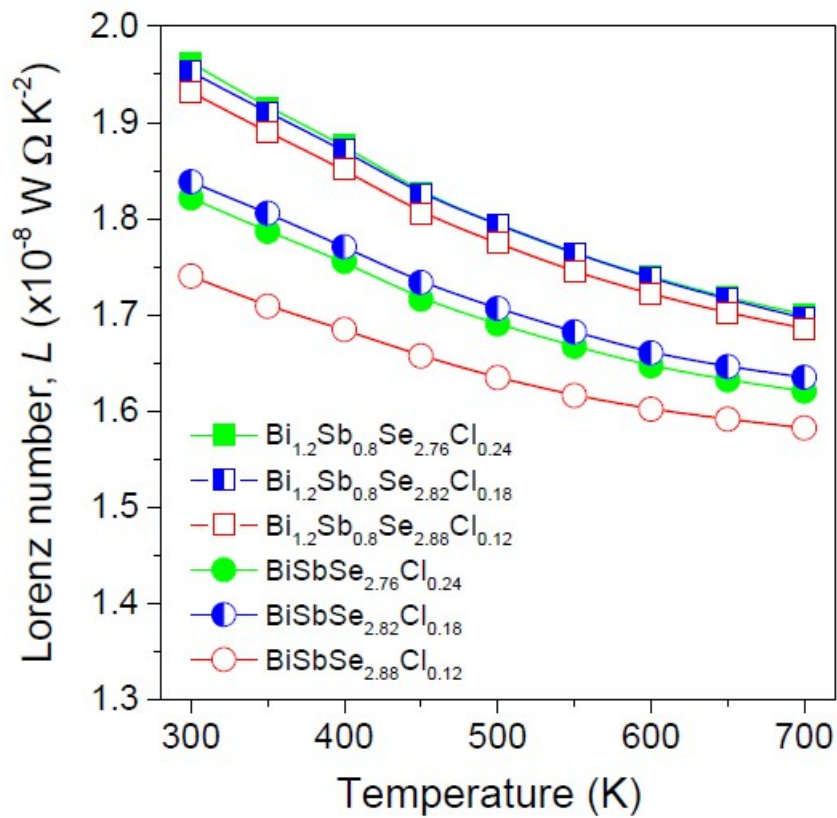


Figure S5. Temperature dependences of L for Cl-doped BiSbSe_3 and $\text{Bi}_{1.2}\text{Sb}_{0.8}\text{Se}_3$.

References

- [1] H. S. Kim, Z. M. Gibbs, Y. Tang, H. Wang, and G. J. Snyder, *APL Mater.* 3 (2015) 041506.